

/ Descriptions

VRW0656 QSQ Silicon NPN transistor in a SOT-323 Plastic Package.

/ Features

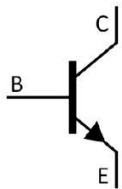
S_F / k_{IH} / $<345 Z$

High P_C and h_{FE} , excellent h_{FE} linearity, complementary pair with 9012W.

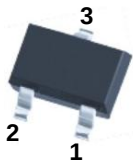
/ Applications

Amplifier of portable radios in class B push-pull operation.

/ Equivalent Circuit



/ Pinning



PIN1 Emitter PIN 2 Base PIN 3 Collector

/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	D	E	F	G	H	I
h_{FE} Range	64 91	78 112	96 135	112 166	144 202	188 276
Marking	HJ3D	HJ3E	HJ3F	HJ3G	HJ3H	HJ3I

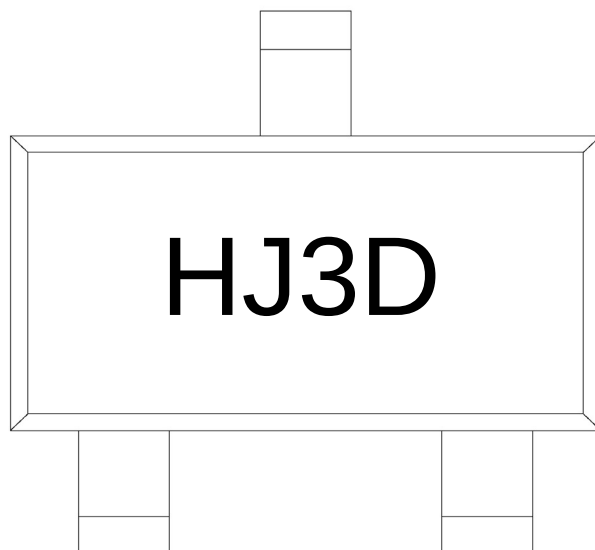
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	20	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current	I_C	500	mA
Base Current	I_B	100	mA
Collector Power Dissipation	P_C	350	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=0.1mA$ $I_E=0$	40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=1.0mA$ $I_B=0$	20			V

/ Electrical Characteristic Curve



/ Marking Instructions



K

M6

G h_{FE}

Note:

K Company Code

M6 Product Type Code

G h_{FE} Classifications Symbol Code

